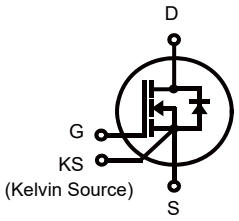
DACMI120N200BZK2

SiC MOSFET Power Module

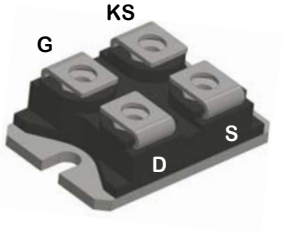
Preliminary

Features

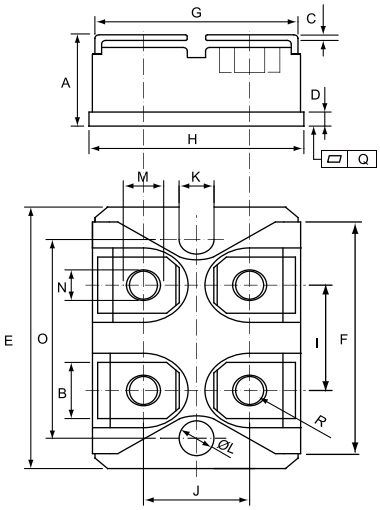
- V_{DSS} = 2000V
- $R_{DS(ON)}$ typ. 16mΩ@ V_{GS} = 18V
- High speed switching with low capacitances
- Easy to parallel and simple to drive
- Real Kelvin Source Connection
- Pb Free & RoHS Compliant
- Electrically Isolation base plate



SOT-227



Dimensions in inches and (millimeters)



Applications

- Solar Inverters
- UPS
- Motor Drive
- Induction heating
- Switch Mode Power Supplies
- Battery Chargers
- DC/DC Converters

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	2000	V
Gate-Source Voltage (dynamic)		$V_{GS(max)}$	-10/+23	V
Gate-Source Voltage (static)		$V_{GS(OP)}$	-4/+18	V
Drain Current-Continuous	@ T_C =25°C @ T_C =100°C	I_D	170 120	A
Drain Current-Pulsed	@ T_C =25°C	I_{DM}	340	A
Maximum Power Dissipation		P_D	680	W
Storage Temperature Range		T_{STG}	-40 to +125	°C
Operating Junction Temperature Range		T_{VJ}	-40 to +175	°C
Thermal Resistance, Junction-to-Case		$R_{\theta JC}$	0.22	°C/W
Isolation Voltage (A.C. 1 minute) between All Terminals and Baseplate		V_{iso}	2500	V
Mounting torque (M4 Screw)	To heatsink To terminals	M_d	1.3 1.1	N m

DIMENSIONS				
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			

Electrical Characteristics @ T_{VJ} =25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
OFF Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V，I_{DS}=0.2mA		2000	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V，V_{DS}=2000V		-	-	200	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=20V，V_{DS}=0V		-	-	500	nA
ON Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}，I_{DS}=8mA		2.2	3.2	4.6	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=18V，I_{DS}=75A		-	16	20.8	mΩ
Gate Resistance	$R_{G(int)}$	Internal gate resistor	T_{VJ} =25°C	-	5.73	-	Ω
Dynamic Characteristics							
Input Capacitance	C_{iss}	V_{DS}=800V V_{GS}=0V V_{AC}=1V Freq.=100KHz		-	8.8	-	nF
Output Capacitance	C_{oss}			-	0.28	-	
Reverse Transfer Capacitance	C_{rss}			-	0.036	-	
Total Gate Charge	Q_g	V_{DS}=1000V V_{GS}=-4V/+18V I_{DS}=120A		-	328	-	nC
Gate to Source Charge	Q_{gs}			-	174	-	
Gate to Drain Charge	Q_{gd}			-	77	-	
Switching Characteristics							
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 1000V V_{GS} = -4V/+18V I_{DS}=120A $R_{G(on)}$=1.0Ω $R_{G(off)}$=1.0Ω	T_{VJ} =25°C	-	85	-	ns
			T_{VJ} =150°C	-	76	-	
Rise Time	t_r		T_{VJ} =25°C	-	87	-	
			T_{VJ} =150°C	-	94	-	
Turn-Off Delay Time	$t_{d(off)}$		T_{VJ} =25°C	-	158	-	
			T_{VJ} =150°C	-	183	-	
Fall Time	t_f		T_{VJ} =25°C	-	23	-	
			T_{VJ} =150°C	-	24	-	
Turn-On Switching Energy	E_{on}	V_{DD} = 1000V V_{GS} = -4V/+18V I_{DS}=120A $R_{G(on)}$=1.0Ω $R_{G(off)}$=1.0Ω	T_{VJ} =25°C	-	4.3	-	mJ
			T_{VJ} =150°C	-	5.8	-	
Turn-Off Switching Energy	E_{off}		T_{VJ} =25°C	-	5.4	-	
			T_{VJ} =150°C	-	6.2	-	
Body Diode Characteristics at T_J = 25° C, unless otherwise specified							
Continuous Diode Fwd Current	I_{SDC}	V_{GS} = 0V		-	120	-	A
Drain-Source Reverse Voltage	V_{SD}	I_{SD} = 100A , V_{GS} = 0V		-	4.5	-	V
MOSFET Forward Recovery Charge	Q_{rr}	V_{DD} = 1000V I_{SD} =120A V_{GS} = -4V/+18V di/dt = 2880 A/μs	T_{VJ} =25°C	-	125	-	nC
			T_{VJ} =150°C	-	2137	-	
MOSFET Peak Forward Recovery Current	Irrm		T_{VJ} =25°C	-	12	-	A
			T_{VJ} =150°C	-	56	-	
MOSFET Reverse Recovery Time	T_{rr}		T_{VJ} =25°C	-	17	-	ns
			T_{VJ} =150°C	-	61	-	

Notes:

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle > 2%.

Typical Characteristics

Fig.1 Output Characteristics at T_J = 25°C

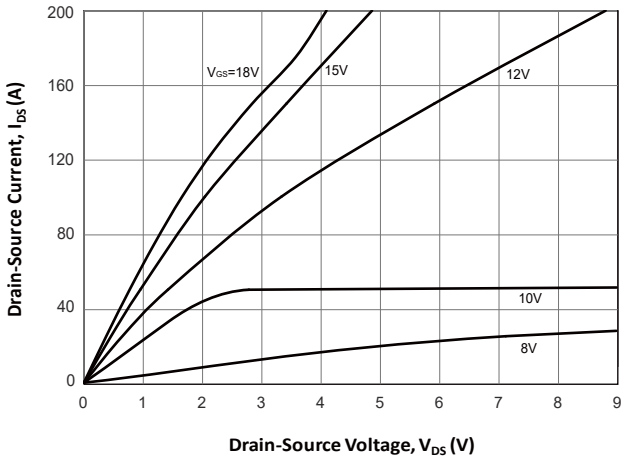


Fig.2 Output Characteristics at T_J =125°C

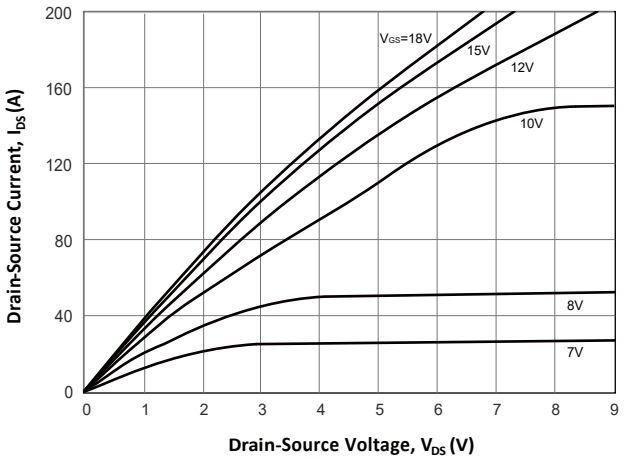


Fig.3 Drain Source on Resistance

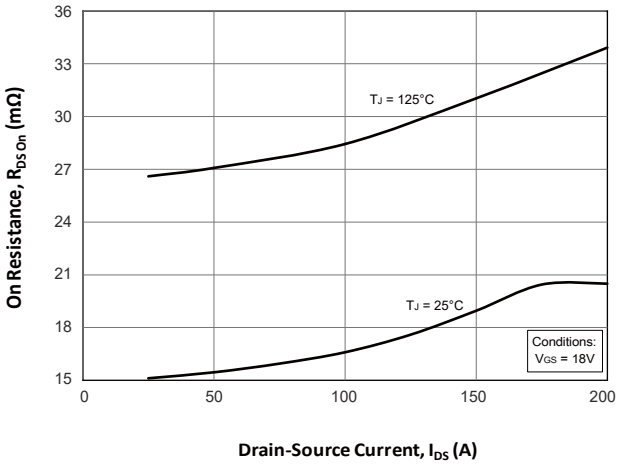


Fig.4 Transfer Characteristics

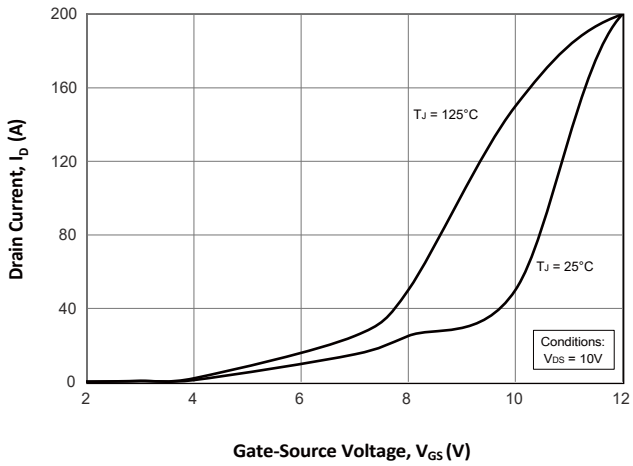


Fig.5 Capacitances vs. Drain-Source Voltage

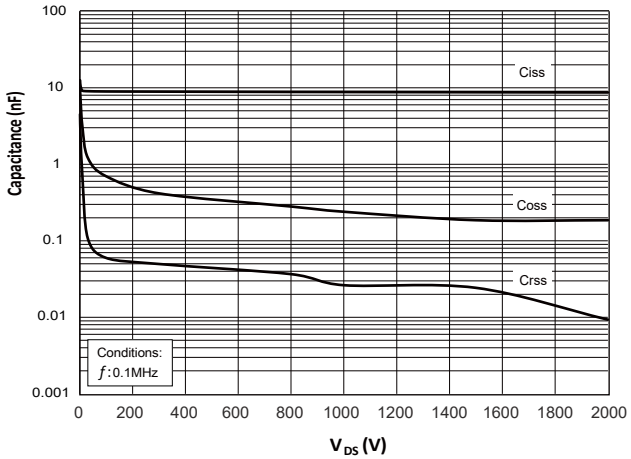
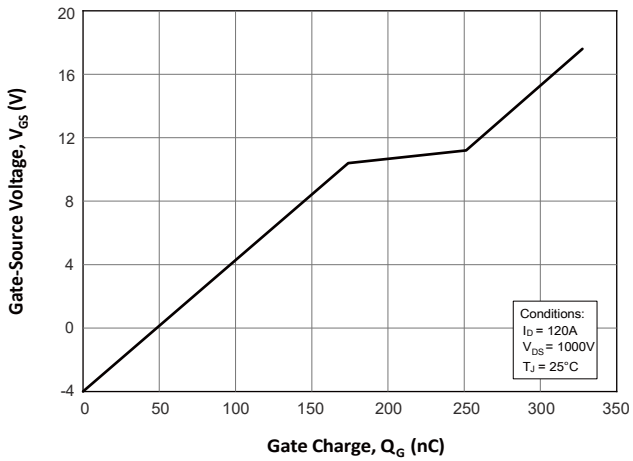


Fig.6 Gate Charge Characteristics



Typical Characteristics

Fig.7 Switching losses vs R_G change T_J=125°C

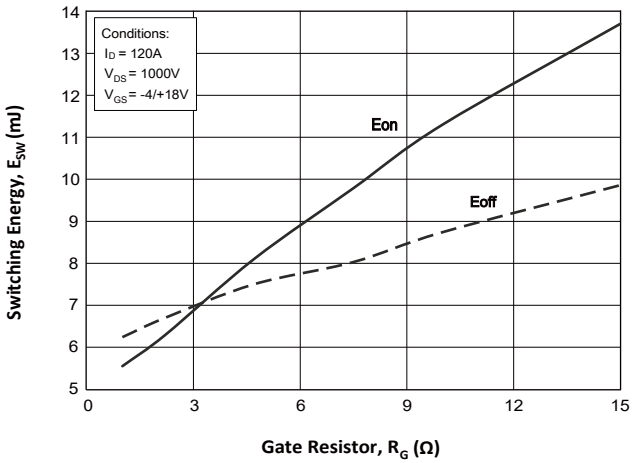


Fig.8 Switching losses vs R_G change T_J=150°C

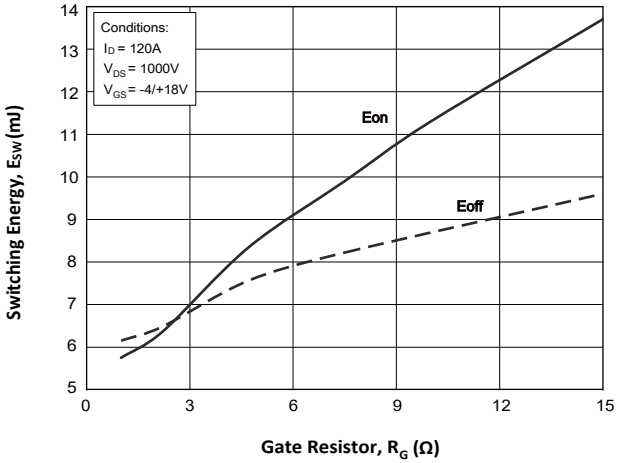


Fig.9 Switching Timer vs R_G Change T_J=125°C

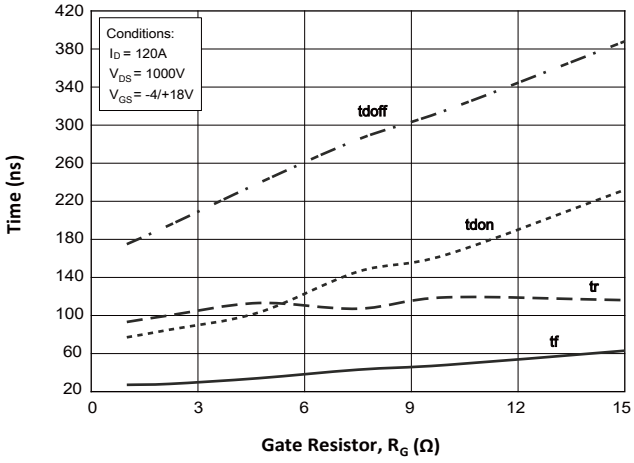


Fig.10 Switching Timer vs R_G Change T_J=150°C

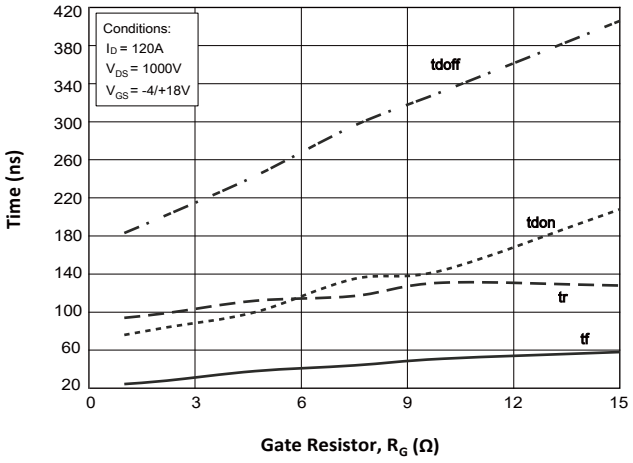


Fig.11 Clamped Inductive Switching Energy vs. Drain Current T_J =125°C

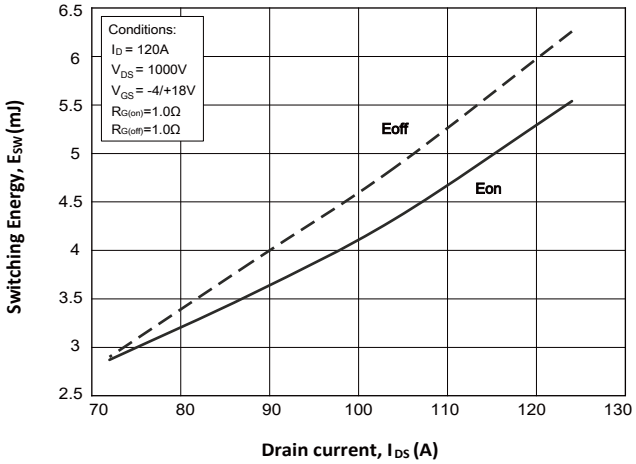
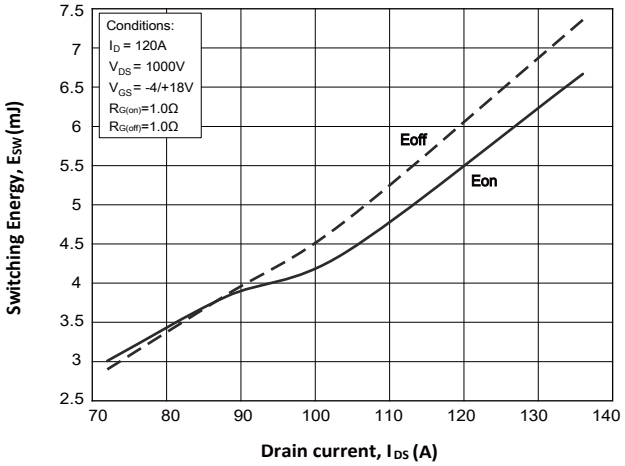


Fig.12 Clamped Inductive Switching Energy vs. Drain Current T_J =150°C



Typical Characteristics

Fig.13 Body Diode curves T_J =25°C

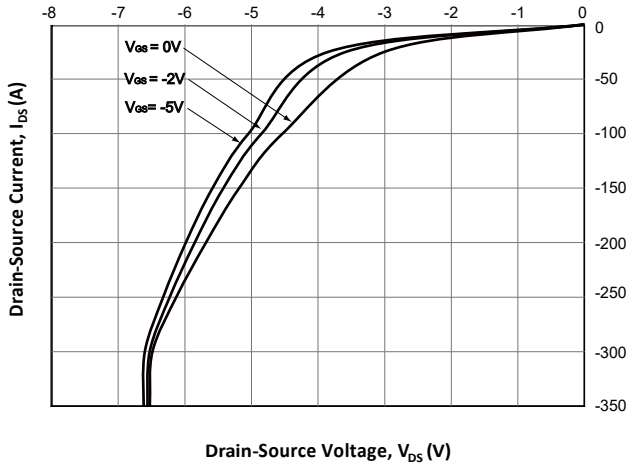


Fig.14 Body Diode curves T_J = 125°C

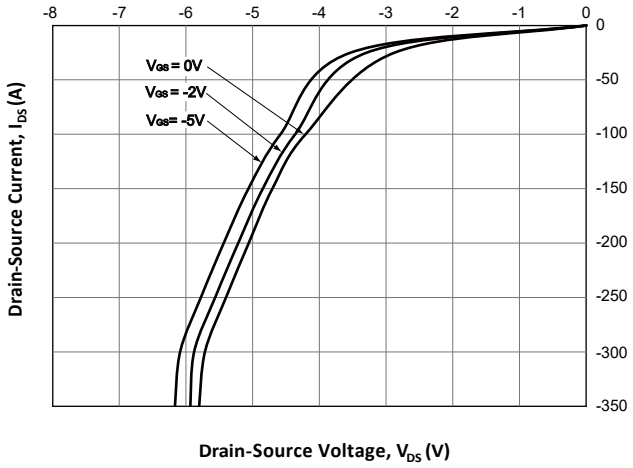


Fig.15 Continuous Drain Current (MOSFET) vs. Case Temperature

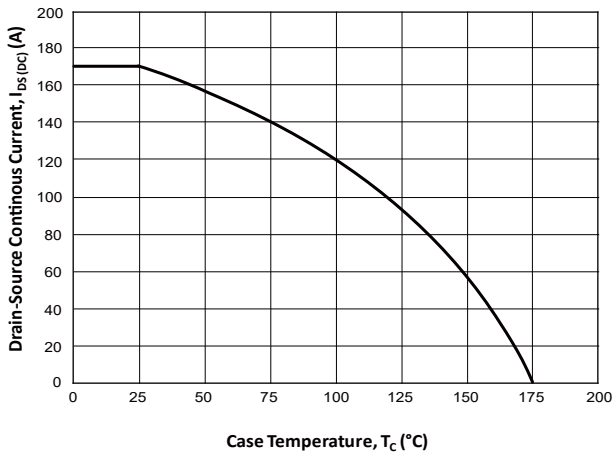
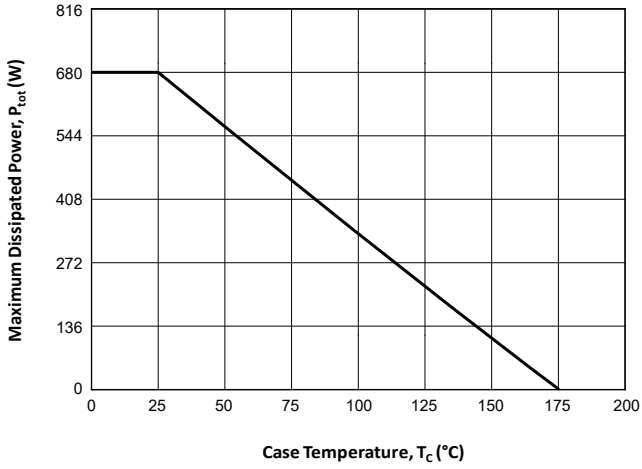


Fig.16 Max. Power Dissipation (MOSFET) Derating vs. Case Temperature



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